This Class 216 is considered to be an integral part of Class 156 (see the Class 156 schedule for the position of this Class in schedule hierarchy). This Class retains all pertinent definitions and class lines of Class 156.

2 **ETCHING OF SEMICONDUCTOR MATERIAL TO PRODUCE AN ARTICLE HAVING A NONELECTRICAL FUNCTION**

3 **FORMING OR TREATING JOSEPHSON JUNCTION ARTICLE**

4 **FORMING OR TREATING A SIGN OR MATERIAL USEFUL IN A SIGN**

5 .Sign or material is electroluminescent

6 **FORMING OR TREATING MATERIAL USEFUL IN A CAPACITOR**

7 **FORMING OR TREATING FIBROUS ARTICLE OR FIBER REINFORCED COMPOSITE STRUCTURE**

8 **FORMING OR TREATING CYLINDRICAL OR TUBULAR ARTICLE HAVING PATTERN OR DESIGN ON ITS SURFACE**

9 .Forming or treating an embossing cylinder or tubular article

10 .Forming or treating liquid transfer cylinder or tubular article (e.g., printing roll, etc.)

11 **FORMING OR TREATING AN ARTICLE WHOSE FINAL CONFIGURATION HAS A PROJECTION**

12 **FORMING OR TREATING MASK USED FOR ITS NONETCHING FUNCTION (E.G., SHADOW MASK, X-RAY MASK, ETC.)**

13 **FORMING OR TREATING ELECTRICAL CONDUCTOR ARTICLE (E.G., CIRCUIT, ETC.)**

14 .Forming or treating lead frame or beam lead

15 .Forming or treating a crossover

16 .Forming or treating resistive material

17 .Forming or treating of groove or through hole

18 ..Filling or coating of groove or through hole with a conductor to form an electrical interconnection

19 ..Filling or coating of groove or through hole in a conductor with an insulator

20 .Adhesive or autogenous bonding of self-sustaining preforms (e.g., prefabricated base, etc.)

21 .Repairing circuit

22 **FORMING OR TREATING ARTICLE CONTAINING MAGNETICALLY RESPONSIVE MATERIAL**

23 **FORMING OR TREATING ARTICLE CONTAINING A LIQUID CRYSTAL MATERIAL**

24 **FORMING OR TREATING OPTICAL ARTICLE**

25 .Phosphor screen

26 .Lens

27 **FORMING OR TREATING THERMAL INK JET ARTICLE (E.G., PRINT HEAD, LIQUID JET RECORDING HEAD, ETC.)**

28 **FORMING OR TREATING AN ORNAMENTED ARTICLE**

29 .Wood surface treated or wood grain produced

30 .Treating stone (e.g., marble, etc.)

31 .Treating glass (e.g., mirror, etc.)

32 .Treating elemental metal or alloy thereof

33 **ADHESIVE OR AUTOGENOUS BONDING OF TWO OR MORE SELF-SUSTAINING PREFORMS WHEREIN AT LEAST TWO OF THE PREFORMS ARE NOT INTENDED TO BE REMOVED (E.G., PREFABRICATED BASE, ETC.)**

34 .Etching improves or promotes adherence of preforms being bonded

35 ..Bonding of preform of metal or an alloy thereof to a preform of a nonmetal

36 .Removing at least one of the self-sustaining preforms or a portion thereof

37 **ETCHING AND COATING OCCUR IN THE SAME PROCESSING CHAMBER**

38 **PLANARIZING A NONPLANAR SURFACE**

39 **FORMING GROOVE OR HOLE IN A SUBSTRATE WHICH IS SUBSEQUENTLY FILLED OR COATED**

40 **FORMING PATTERN USING LIFT OFF TECHNIQUE**
41 **MASKING OF A SUBSTRATE USING MATERIAL RESISTANT TO AN ETCHANT (I.E., ETCH RESIST)**
42 .Resist material applied in particulate form or spray
43 .Adhesively bonding resist to substrate
44 .Mechanically forming pattern into a resist
45 .Mask is reusable (i.e., stencil)
46 .Masking of sidewall
47 .Mask is multilayer resist
48 .Mask is exposed to nonimaging radiation
49 .Mask resist contains organic compound
50 ..Mask resist contains a color imparting agent
51 .Mask resist contains inorganic material
52 **MECHANICALLY SHAPING, DEFORMING, OR ABRADING OF SUBSTRATE**
53 .Nongaseous phase etching
54 **PATTERN OR DESIGN APPLIED BY TRANSFER**
55 **HEATING OR BAKING OF SUBSTRATE PRIOR TO ETCHING TO CHANGE THE CHEMICAL PROPERTIES OF SUBSTRATE TOWARD THE ETCHANT**
56 **ETCHING TO PRODUCE POROUS OR PERFORATED ARTICLE**
57 **GAS PHASE AND NONGASEOUS PHASE ETCHING ON THE SAME SUBSTRATE**
58 **GAS PHASE ETCHING OF SUBSTRATE**
59 .With measuring, testing, or inspecting
60 ..By optical means or of an optical property
61 ..By electrical means or of an electrical property
62 .Irradiating, ion implanting, alloying, diffusing, or chemically reacting the substrate prior to etching to change properties of substrate toward the etchant
63 .Application of energy to the gaseous etchant or to the substrate being etched
64 ..Etchant is devoid of chlorocarbon or fluorocarbon compound (e.g., C.F.C., etc.)
65 ..Using laser
66 ..Using ion beam, ultraviolet, or visible light
67 ..Using plasma
68 ...Using coil to generate the plasma
69 ...Using microwave to generate the plasma
70 ....Magnetically enhancing the plasma
71 ...Specific configuration of electrodes to generate the plasma
72 .Etching a multiple layered substrate where the etching condition used produces a different etching rate or characteristic between at least two of the layers of the substrate
73 .Etching vapor produced by evaporation, boiling, or sublimation
74 .Etching inorganic substrate
75 ..Substrate contains elemental metal, alloy thereof, or metal compound
76 ...Etching of substrate containing at least one compound having at least one oxygen atom and at least one metal atom
77 ...Etching of substrate containing elemental aluminum, or an alloy or compound thereof
78 ...Etching of substrate containing elemental copper, or an alloy or compound thereof
79 ..Etching silicon containing substrate
80 ...Silicon containing substrate is glass
81 ..Etching elemental carbon containing substrate
83 **NONGASEOUS PHASE ETCHING OF SUBSTRATE**
84 .With measuring, testing, or inspecting
85 ..By optical means or of an optical property
86 ..By electrical means or of an electrical property

87 .Irradiating, ion implanting, alloying, diffusing, or chemically reacting the substrate prior to ethching to change properties of substrate toward the etchant
88 .Using film of etchant between a stationary surface and a moving surface (e.g., chemical lapping, etc.)
89 ..Etchant contains solid particle (e.g., abrasive for polishing, etc.)
90 .Relative movement between the substrate and a confined pool of etchant
91 ..Rotating, repeated dipping, or advancing movement of substrate
92 .Projecting etchant against a moving substrate or controlling the angle or pattern projection of the etchant or controlling the angle or pattern of movement of the substrate
93 .Recycling, regenerating, or rejunevating etchant
94 .Etching using radiation (e.g., laser, electron-beam, ion-beam, etc.)
95 .Substrate is multilayered
96 .Etching inorganic substrate
97 ..Substrate is glass
98 ...Frosting glass
99 ..Substrate contains silicon or silicon compound
100 ..Substrate contains elemental metal, alloy thereof, or metal compound
101 ...Etching of a compound containing at least one oxygen atom and at least one metal atom
102 ...Metal is elemental aluminum, an alloy, or compound thereof
103 ....Etchant contains acid
104 .....Etchant contains fluoride ion
105 ...Metal is elemental copper, an alloy, or compound thereof
106 ....Etchant contains acid
107 .....Etchant contains fluoride ion
108 ...Etchant contains acid
109 ....Etchant contains fluoride ion

FOREIGN ART COLLECTIONS

FOR 000 **CLASS-RELATED FOREIGN DOCUMENTS**